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(54) **SUPER-STEEP SWITCHING DEVICE AND  
INVERTER DEVICE USING THE SAME**

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(57) **ABSTRACT**

A super-steep switching device is provided. The super-steep switching device may include a substrate, a semiconductor channel on the substrate, a source electrode and a drain electrode, which are disposed on the semiconductor channel and spaced apart from each other, a gate electrode overlapping a portion of the semiconductor channel and not overlapping a remaining portion of the semiconductor channel, and an insulating layer disposed between the gate electrode and the semiconductor channel and covering an entire surface of the semiconductor channel.

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